



ACG: 9H'9@97HF=75@'7&lt;5F57H9F-GH=7G'VæMGÍÁ CÁ~ }| ^••Á[c@^! , ä•^Á•] ^&amp;ä-ä^ä'

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit	
Drain-Source Breakdown Voltage	V <sub>DSS</sub>	I <sub>D</sub> =250 μ A, V <sub>GS</sub> =0V	-30			V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V			-1	μ A	
		V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C			-5		
Gate-Body leakage current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA	
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =-250 μ A	-1	-1.9	-3	V	
Static Drain-Source On-Resistance	r <sub>Ds(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-2.6A		97	130	m Ω	
		V <sub>GS</sub> =-10V, I <sub>D</sub> =-2.6A T <sub>J</sub> =125°C		135	150		
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2A		166	200	m Ω	
On state drain current	I <sub>D(ON)</sub>	V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-5V	-5			A	
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> =-5V, I <sub>D</sub> =-5A	3	3.8		S	
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =-15V, f=1MHz		302	370	pF	
Output Capacitance	C <sub>oss</sub>			50.3		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			37.8		pF	
Gate resistance	R <sub>g</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		12	18	Ω	
Total Gate Charge (10V)	Q <sub>g</sub>	V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-15V, I <sub>D</sub> =-2.6A		6.8	9	nC	
Total Gate Charge (4.5V)				2.4		nC	
Gate Source Charge	Q <sub>gs</sub>			1.6		nC	
Gate Drain Charge	Q <sub>gd</sub>			0.95		nC	
Turn-On DelayTime	t <sub>D(on)</sub>		V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, R <sub>L</sub> =5.8 Ω, R <sub>GEN</sub> =3 Ω		7.5		ns
Turn-On Rise Time	t <sub>r</sub>				3.2		ns
Turn-Off DelayTime	t <sub>D(off)</sub>			17		ns	
Turn-Off Fall Time	t <sub>f</sub>			6.8		ns	
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =-2.6A, di/dt=100A/ μ s		16.8	22	ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =-2.6A, di/dt=100A/ μ s		10		nC	
Maximum Body-Diode Continuous Current	I <sub>S</sub>				-2	A	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V		-0.82	-1	V	

\* Repetitive rating, pulse width limited by junction temperature.